

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CBR1F-D010 SERIES

1 AMP DUAL IN LINE
FAST RECOVERY
SILICON BRIDGE RECTIFIER

DIP CASE

DESCRIPTION

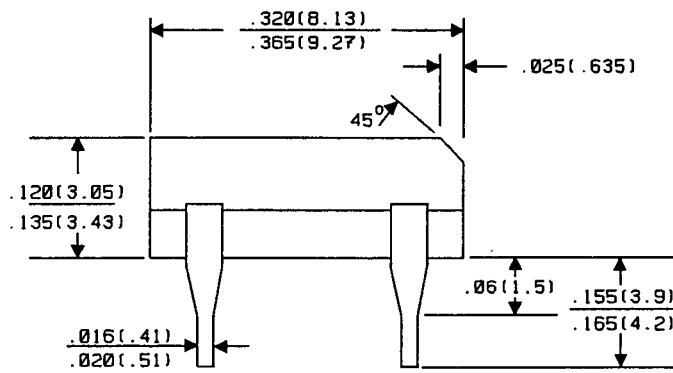
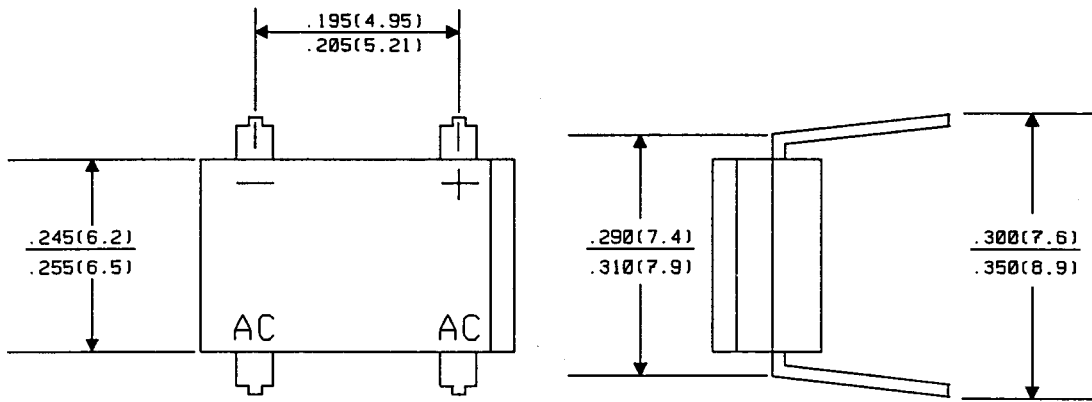
The CENTRAL SEMICONDUCTOR CBR1F-D010 series types are Silicon Full Wave Bridge Rectifiers mounted in a durable epoxy molded case. This device is ideal for printed circuit board mounting and fits into a standard DIP socket (0.1"/2.54mm spacing).

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

	SYMBOL	CBR1F -D010	CBR1F -D020	CBR1F -D040	CBR1F -D060	CBR1F -D080	CBR1F -D100	UNITS
Peak Repetitive Reverse Voltage	V _{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V _R	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	70	140	280	420	560	700	V
Average Forward Current (T _A = 50°C)	I _O			1.0				A
Peak Forward Surge Current	I _{FSM}			50				A
Operating and Storage Junction Temperature	T _J , T _{stg}			-65 to +150				°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V _F	I _F = 1.0A		1.3	V
I _R	V _R = Rated V _{RRM}		10	μA
I _R	V _R = Rated V _{RRM} , T _A = 100°C		1.0	mA
t _{rr} (100V thru 400V)	I _F = 0.5A, I _R = 1.0A, Recov. to 0.25A		200	ns
t _{rr} (600V)	I _F = 0.5A, I _R = 1.0A, Recov. to 0.25A		300	ns
t _{rr} (800V, 1000V)	I _F = 0.5A, I _R = 1.0A, Recov. to 0.25A		500	ns



All Dimensions in Inches (mm).